



SOT-23 Plastic-Encapsulate Transistor (NPN)

Feature

- Complementary to BCW68
- BCW66 is subdivided into three groups F,G and H according to DC current gain

Mechanical Data

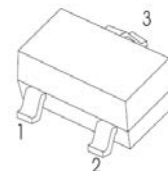
- SOT-23 Small Outline Plastic Package
- Epoxy UL: 94V-0
- Mounting Position: Any

Maximum Rating ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	75	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	800	mA
P_C	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	625	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

SOT-23

1. BASE
2. EMITTER
3. COLLECTOR

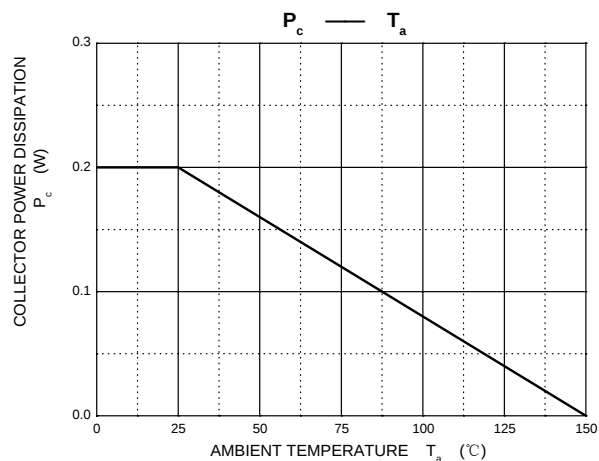
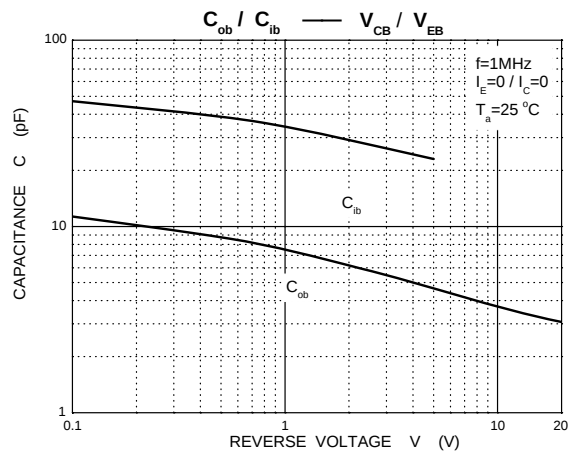
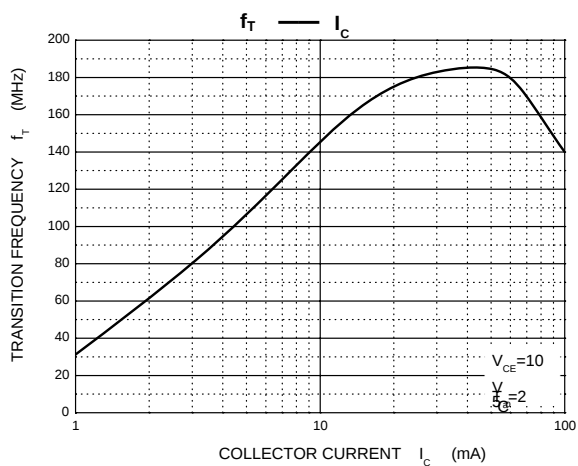
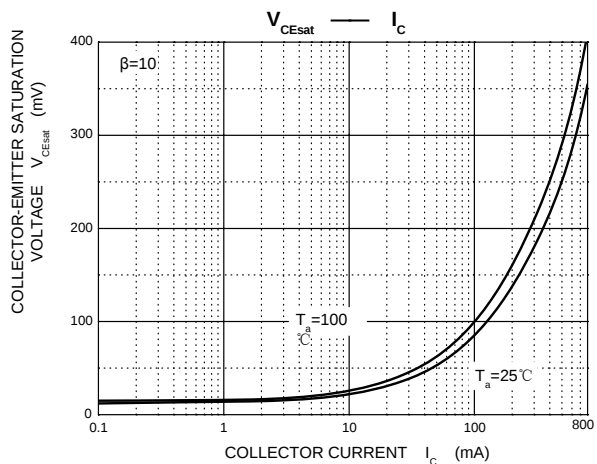
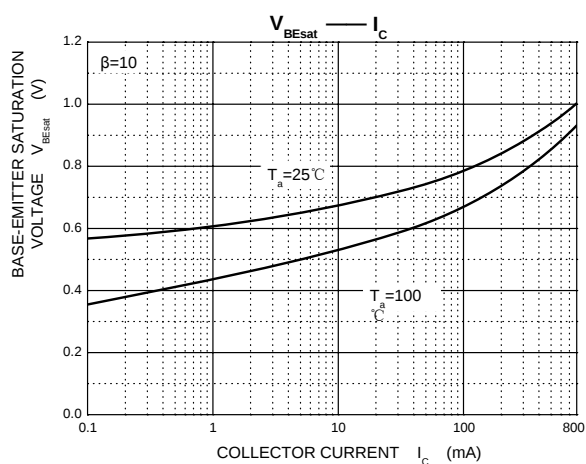
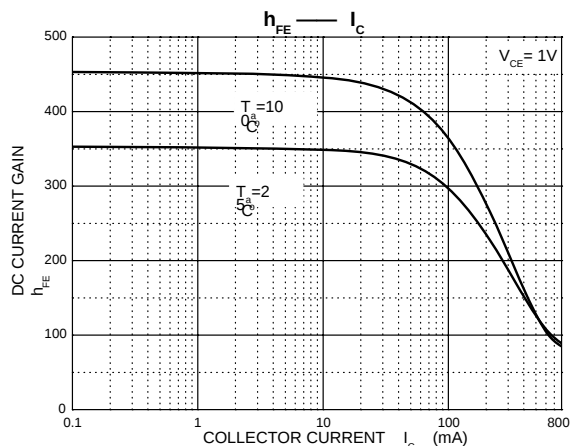
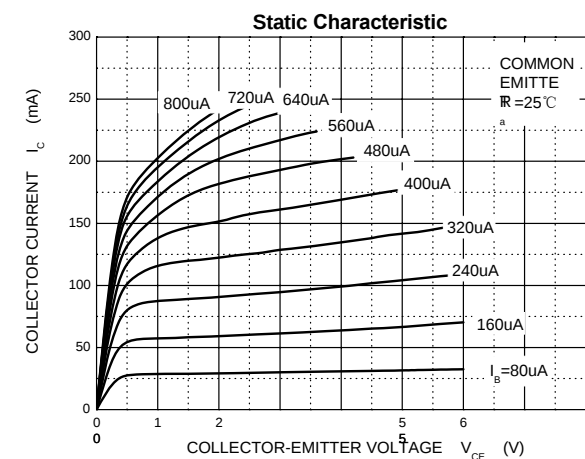


Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	75			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=45\text{V}, I_E=0$			0.02	μA
Collector cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.02	μA
DC current gain	h_{FE1}	$V_{CE}=10\text{V}, I_C=0.1\text{mA}$	BCW66-F BCW66-G BCW66-H	35 50 80		
	h_{FE2}	$V_{CE}=1\text{V}, I_C=10\text{mA}$	BCW66-F BCW66-G BCW66-H	75 110 180		
	h_{FE3}	$V_{CE}=1\text{V}, I_C=100\text{mA}$	BCW66-F BCW66-G BCW66-H	100 160 250	250 400 630	
	h_{FE4}	$V_{CE}=2\text{V}, I_C=500\text{mA}$	BCW66-F BCW66-G BCW66-H	35 60 100		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=10\text{mA}$			0.3	V
		$I_C=500\text{mA}, I_B=50\text{mA}$			0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$			2	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=20\text{mA}, f=100\text{MHz}$	100			MHz
Output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$			12	pF
Input capacitance	C_{ib}	$V_{EB}=0.5\text{V}, I_E=0, f=1\text{MHz}$			80	pF
Noise figure	NF	$V_{CE}=5\text{V}, I_C=0.2\text{mA}, f=1\text{KHz}, R_S=1\text{K}\Omega, BW=200\text{Hz}$			10	dB

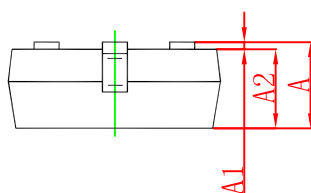
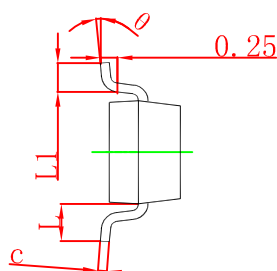
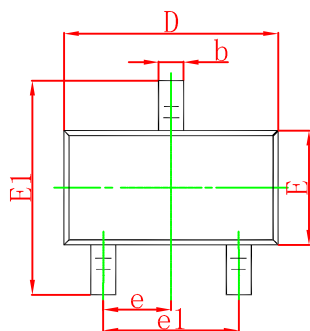


Typical Characteristics



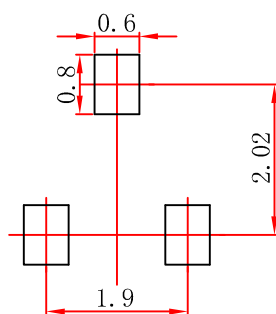


SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Notes:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

Classification of h_{FE}

Rank	BCW66-F	BCW66-G	BCW66-H
Range	100~250	160~400	250~630
Marking	EF	EG	EH